



Si2306BDS vs. Si2306DS

Description: N-Channel, 30 V (D-S) MOSFET

Package: SOT-23

Pin Out: Identical

Part Number Replacements:

Si2306BDS-T1-E3 Replaces Si2306DS-T1-E3

Si2306BDS-T1-E3 Replaces Si2306DS-T1

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted					
Parameter	Symbol	Si2306BDS	Si2306DS	Unit	
Drain-Source Voltage	V_{DS}	30	30	V	
Gate-Source Voltage	V_{GS}	± 20	± 20		
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	I_D	4.0	3.5	A
	$T_A = 70\text{ }^\circ\text{C}$		3.5	2.8	
Pulsed Drain Current	I_{DM}	20	16		
Continuous Source Current (MOSFET Diode Conduction)	I_S	1.04	1.25		
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	1.25	1.25	W
	$T_A = 70\text{ }^\circ\text{C}$		0.8	0.8	
Operating Junction and Storage Temperature Range	T_j and T_{stg}	- 55 to 150	- 55 to 150	$^\circ\text{C}$	
Maximum Junction-to-Ambient	R_{thJA}	100	100	$^\circ\text{C/W}$	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Si2306BDS			Si2306DS			Unit
		Min	Typ	Max	Min	Typ	Max	
Static								
Gate-Threshold Voltage	$V_{G(th)}$	1.0		3.0	1.0		NS	V
Gate-Body Leakage	I_{GSS}			± 100			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}			0.5			0.5	μA
On-State Drain Current	$V_{GS} = 10\text{ V}$	$I_{D(on)}$	6		6			A
	$V_{GS} = 4.5\text{ V}$		NS		4			
Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$	$r_{DS(on)}$	0.038	0.047	0.046	0.057		Ω
	$V_{GS} = 4.5\text{ V}$		0.052	0.065	0.070	0.094		
Forward Transconductance	g_{fs}		7			6.9		S
Diode Forward Voltage	V_{SD}		0.8	1.2		0.8	1.2	V
Dynamic								
Input Capacitance	C_{iss}		305			555		pF
Output Capacitance	C_{oss}		65			120		
Reverse Transfer Capacitance	C_{rss}		29			60		
Gate Charge	Q_g		3.0	4.5		4.2	7	nC
Total Gate Charge	Q_{gt}		6	9		8.5	20	
Gate-Source Charge	Q_{gs}		1.6			1.9		
Gate-Drain Charge	Q_{gd}		0.6			1.35		
Gate Resistance	R_g	2.5	5.0	7.5	0.5	NS	2.4	Ω
Switching								
Turn-On Time*	$t_{d(on)}$		7	11		9	20	ns
	t_r		12	18		7.5	18	
Turn-Off Time*	$t_{d(off)}$		14	25		17	35	
	t_f		6	10		5.2	12	

NS denotes not specified in datasheet.

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.